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FDA16N50_F109 N-Channel UniFETTM MOSFET 500V, 16.5 A, 380 mΩ

Features

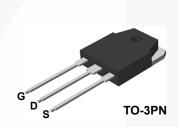
- $R_{DS(on)}$ = 380 m Ω (Max.) @ V_{GS} = 10, I_D = 8.3 A
- Low Gate Charge (Typ. 32 nC)
- Low C_{rss} (Typ. 20 pF)
- 100% Avalanche Tested

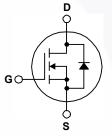
Applications

- PDP TV
- Uninterruptible Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDA16N50_F109	Unit	
V _{DSS}	Drain-Source Voltag	e		500	V	
ID	Drain Current	- Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$)		16.5 9.9	A A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	66	А	
V _{GSS}	Gate-Source voltage			±30	V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	780	mJ	
I _{AR}	Avalanche Current		(Note 1)	16.5	A	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	20.5	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns	
P _D	Power Dissipation	(T _C = 25°C) - Derate above 25°C		205 2.1	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
Τ _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C	

Thermal Characteristics

Symbol	Parameter	FDA16N50_F109	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.6	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	40		

Device i	annig	Device	1 aur	aye	ILEEI SIZE	ιαρ	e Wiutii Quali		lity	
FDA16N50		FDA16N50_F109	TO-3PN		Tube		N/A		30 units	
Electric	al Cha	racteristics ⊤ _c	= 25°C unl	ess otherw	vise noted.					
Symbol		Parameter			Conditions		Min.	Тур.	Max	Unit
Off Charac	teristics									
BV _{DSS}	Drain-Source Breakdown Voltage			V _{GS} = 0V,	I _D = 250μA		500			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient			$I_D = 250\mu A$, Referenced to $25^{\circ}C$				0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current			$V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, T_{C} = 125^{\circ}C$					1 10	μΑ μΑ
I _{GSSF}	Gate-Bod	ly Leakage Current, F	orward	V _{GS} = 30V	, V _{DS} = 0V			-	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse		Reverse	$V_{GS} = -30V, V_{DS} = 0V$					-100	nA
On Charact	teristics									
V _{GS(th)}	Gate Threshold Voltage			V _{DS} = V _{GS}	, I _D = 250μA		3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance			V _{GS} = 10V, I _D = 8.3A				0.31	0.38	Ω
9 _{FS}	Forward Transconductance			V _{DS} = 40V, I _D = 8.3A			23		S	
Dynamic C	haracteris	stics								
C _{iss}	Input Cap	t Capacitance		V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz			1495	1945	pF	
C _{oss}	Output Capacitance Reverse Transfer Capacitance						235	310	pF	
C _{rss}							20	30	pF	
Switching	Character	istics								
t _{d(on)}	Turn-On Delay Time			V _{DD} = 250V, I _D = 16A			40	90	ns	
t _r	Turn-On I	Rise Time		$R_{G} = 25\Omega$			150	310	ns	
t _{d(off)}	Turn-Off I	Delay Time						65	140	ns
t _f	Turn-Off I	Fall Time		(Note 4		(Note 4)		80	170	ns
Qg	Total Gate	e Charge		V _{DS} = 400V, I _D = 16A V _{GS} = 10V (Note 4)			32	45	nC	
Q _{gs}	Gate-Sou	Irce Charge					8.5		nC	
Q _{gd}	Gate-Dra	in Charge					14		nC	
Drain-Sour	ce Diode (Characteristics and	Maximum	Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current							9.2	А	
I _{SM}	Maximum Pulsed Drain-Source Diode Fo			orward Current					37	А
V _{SD}	Drain-Sou	urce Diode Forward V	oltage	V _{GS} = 0V,	I _S = 16.5A				1.4	V
t _{rr}	Reverse	Recovery Time		V _{GS} = 0V,				490	-	ns
Q _{rr}	Reverse	Recovery Charge		dI _F /dt =100A/μs			5.0		μC	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity	
FDA16N50	FDA16N50_F109	TO-3PN	Tube	N/A	30 units	

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. L = 5.1mH, I_{AS} = 16.5A, V_DD = 50V, R_G = 25 Ω , Starting T_J = 25°C

3. I_{SD} \leq 16.5A, di/dt \leq 200A/µs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C

4. Essentially Independent of Operating Temperature Typical Characteristics

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Notes : 1. V_{DS} = 40V

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Notes : 1. V_{GS} = 0V

2.0 2.2 2.4

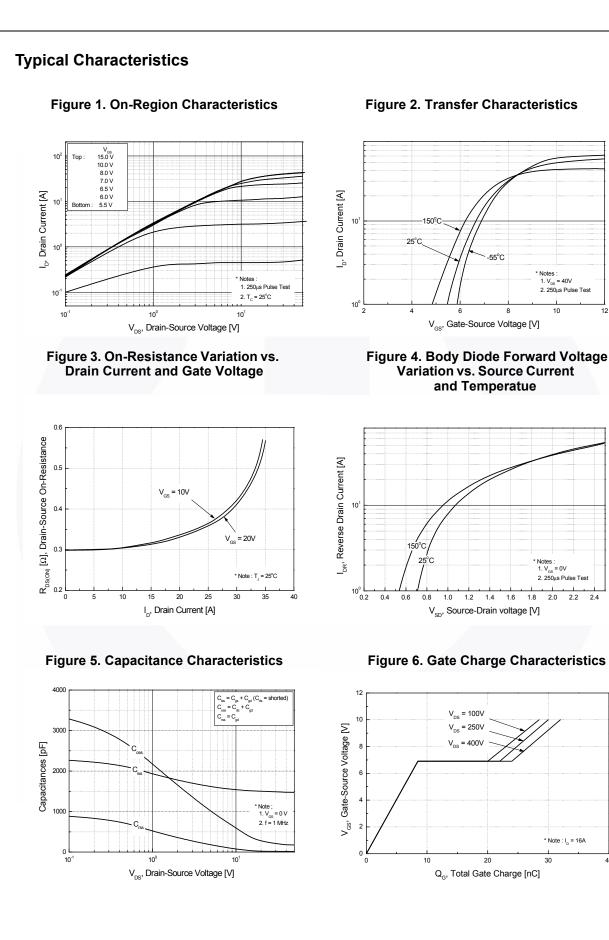
2. 250µs Pulse Tes

* Note : I_p = 16A

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2. 250µs Pulse Test

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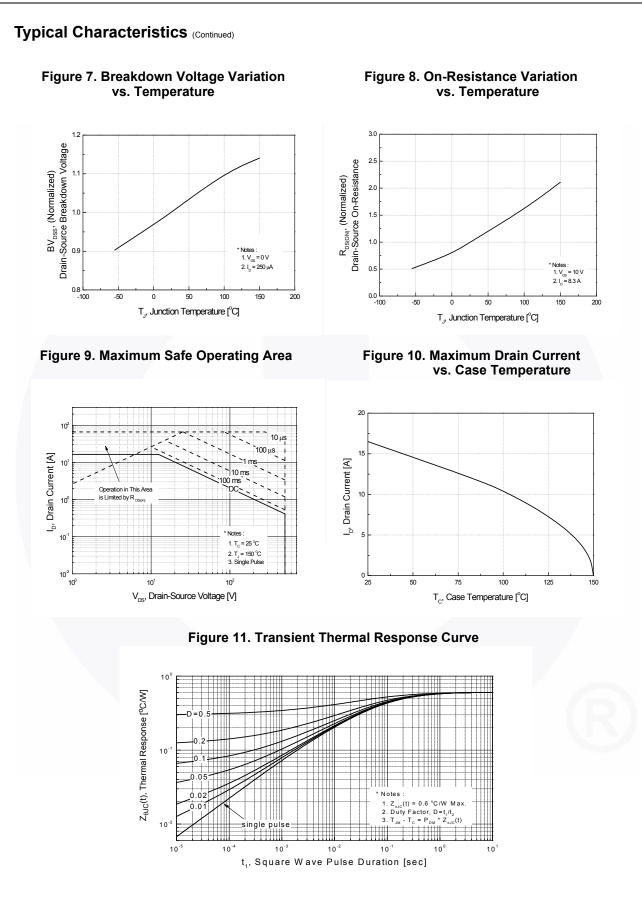


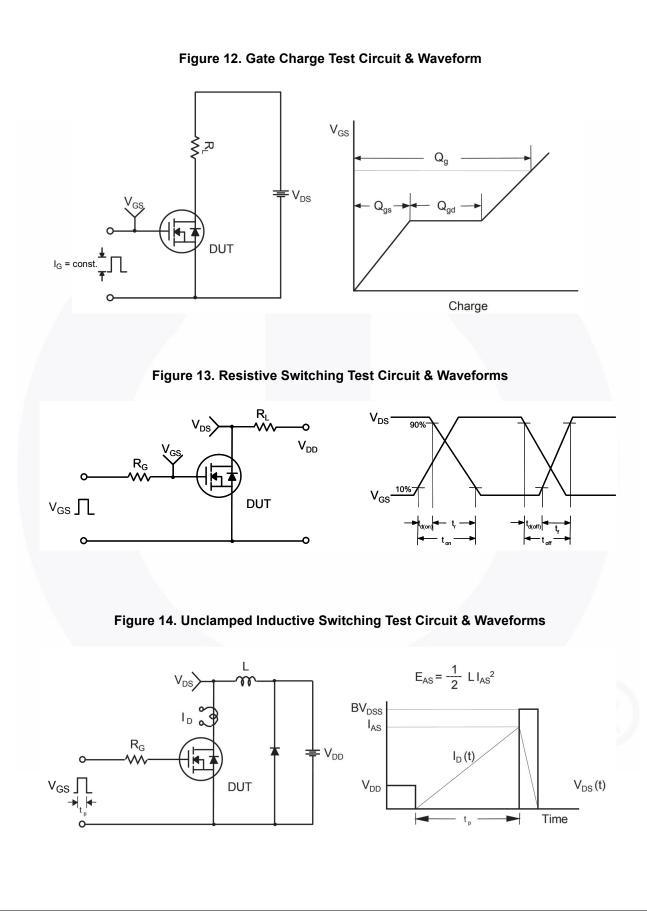
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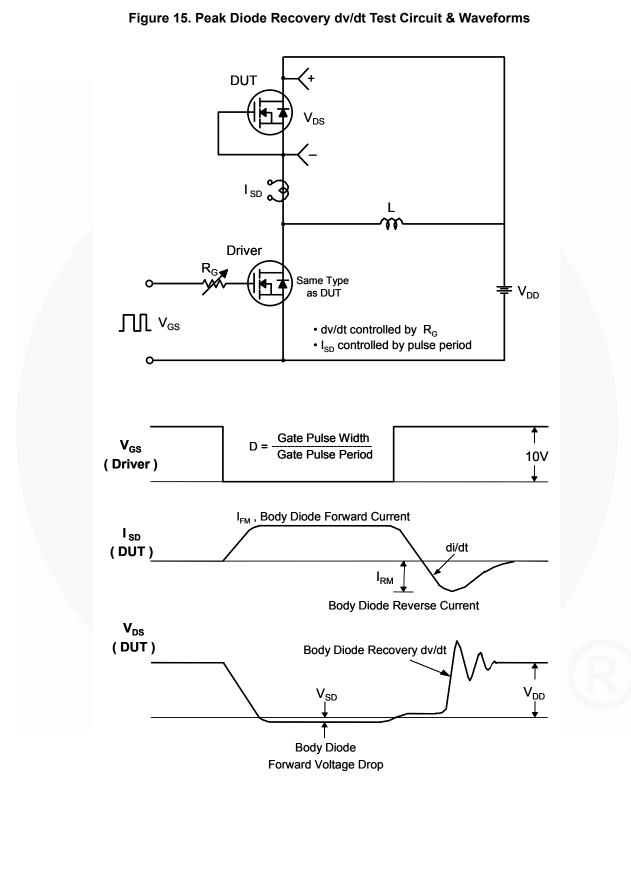
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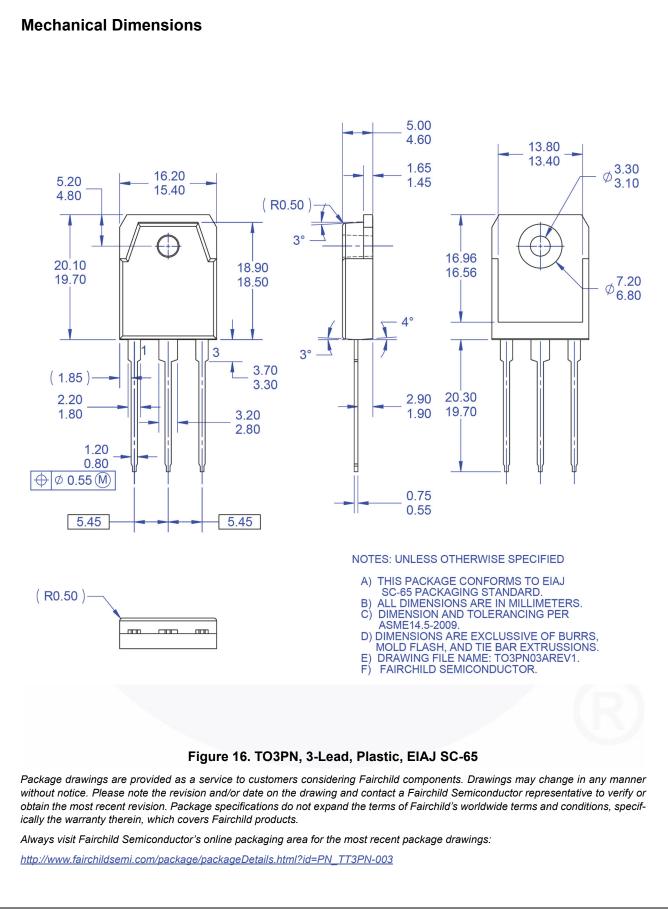
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